

## Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$ max	$I_D$ max
30V	26.5m $\Omega$ @ $V_{GS} = 10V$	5.8A
	32m $\Omega$ @ $V_{GS} = 4.5V$	5.0A

## Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](mailto:contact@diodes.com) or your local Diodes representative. <https://www.diodes.com/quality/product-definitions/>**

## Description and Applications

This MOSFET is designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Battery charging
- Power management functions
- DC-DC converters
- Portable power adaptors

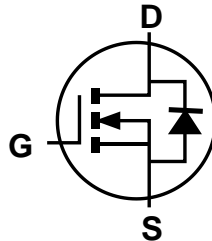
## Mechanical Data

- Package: SOT23 (Standard)
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Annealed over Copper Lead-Frame. Solderable per MIL-STD-202, Method 208
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)

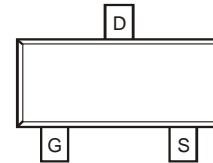
SOT23 (Standard)



Top View



Internal Schematic



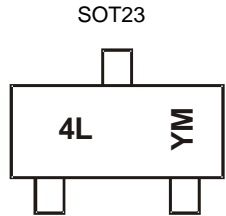
Top View

## Ordering Information

Part Number	Package	Packing	
		Qty.	Carrier
DMN3042L-7	SOT23 (Standard)	3,000	Tape & Reel
DMN3042L-13	SOT23 (Standard)	10,000	Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



4L = Product Type Marking Code  
 YM = Date Code Marking  
 Y or  $\bar{Y}$  = Year (ex: I = 2021)  
 M or  $\bar{M}$  = Month (ex: 9 = September)

### Date Code Key

Year	2017	.....	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	E	.....	I	J	K	L	M	N	O	P	R	S

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

## Maximum Ratings (@ $T_A = +25^\circ\text{C}$ unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			$V_{DSS}$	30	V
Gate-Source Voltage			$V_{GSS}$	$\pm 12$	V
Continuous Drain Current (Note 6) $V_{GS} = 10\text{V}$	Steady State	$T_A = +25^\circ\text{C}$	$I_D$	5.8	A
		$T_A = +70^\circ\text{C}$		4.0	
Maximum Body Diode Forward Current (Note 6)			$I_S$	1.5	A
Pulsed Drain Current (10 $\mu\text{s}$ pulse, duty cycle = 1%)			$I_{DM}$	30	A

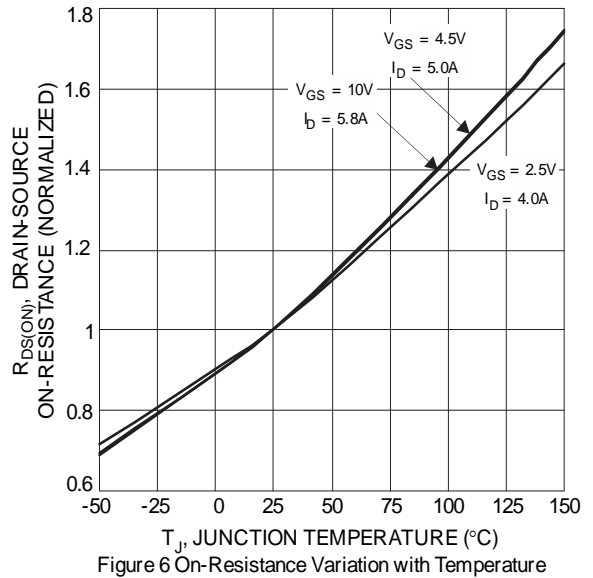
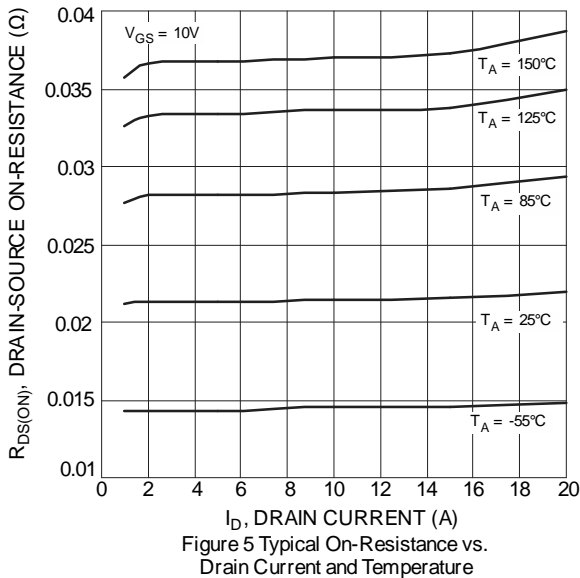
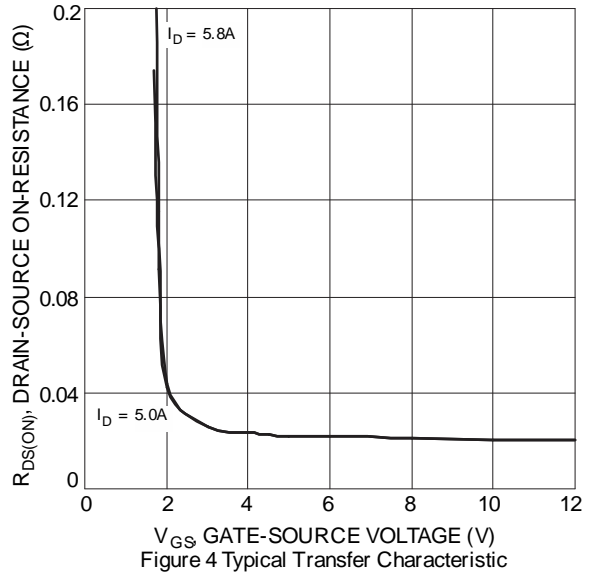
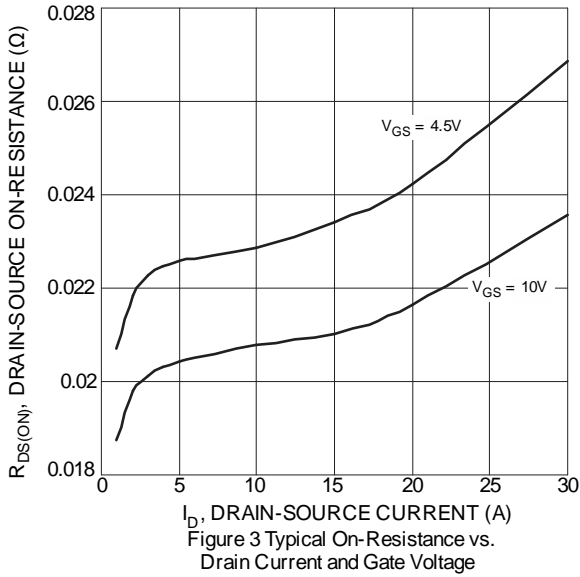
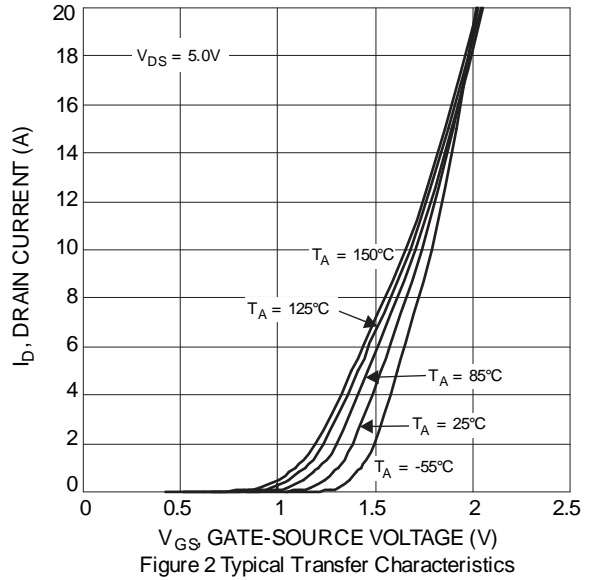
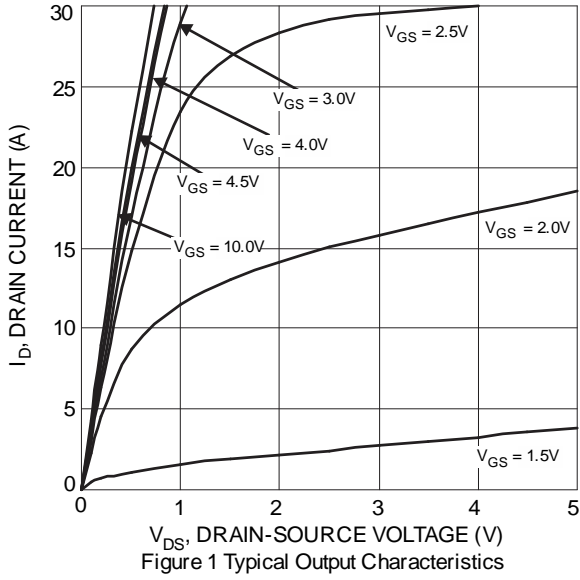
## Thermal Characteristics

Characteristic		Symbol	Value	Unit
Power Dissipation (Note 5)		$P_D$	0.72	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	171	$^\circ\text{C/W}$
Power Dissipation (Note 6)		$P_D$	1.4	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	93	$^\circ\text{C/W}$
Operating and Storage Temperature Range		$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

**Electrical Characteristics** (@ T<sub>A</sub> = +25°C unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±12V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.6	—	1.4	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	—	21	26.5	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 5.8A
		—	23	32		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 5.0A
		—	29	48		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 4.0A
Diode Forward Voltage	V <sub>SD</sub>	—	0.7	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1A
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	—	570	860	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	63	95		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	53	80		
Gate Resistance	R <sub>G</sub>	—	3.2	4.5	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	—	13.3	20	nC	V <sub>DS</sub> = 15V, I <sub>D</sub> = 6.9A
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	6.1	8		
Gate-Source Charge	Q <sub>gs</sub>	—	1.0	1.5		
Gate-Drain Charge	Q <sub>gd</sub>	—	1.6	2.5		
Turn-On Delay Time	t <sub>D(on)</sub>	—	1.5	2.4	nS	V <sub>GS</sub> = 10V, V <sub>DD</sub> = 15V, R <sub>G</sub> = 3Ω, I <sub>D</sub> = 6.9A
Turn-On Rise Time	t <sub>r</sub>	—	3.3	5		
Turn-Off Delay Time	t <sub>D(off)</sub>	—	13.9	22		
Turn-Off Fall Time	t <sub>f</sub>	—	4.9	7		
Body Diode Reverse Recovery Time	t <sub>rr</sub>	—	7.8	12	nS	I <sub>S</sub> = 5A, dI/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	—	1.9	3	nC	I <sub>S</sub> = 5A, dI/dt = 100A/μs

- Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
  7. Short duration pulse test used to minimize self-heating effect.
  8. Guaranteed by design. Not subject to product testing.



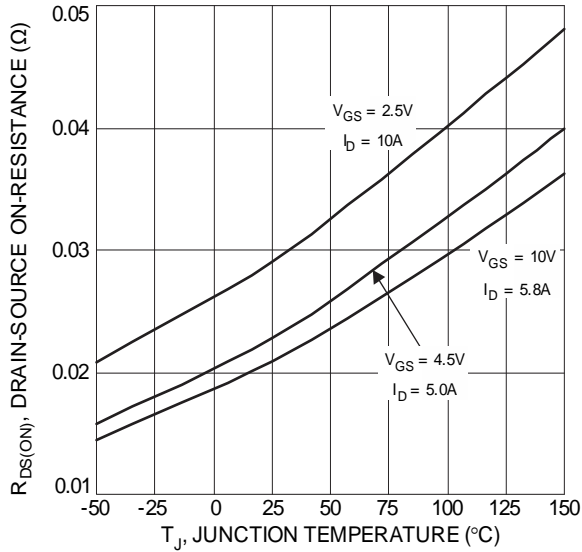


Figure 7 On-Resistance Variation with Temperature

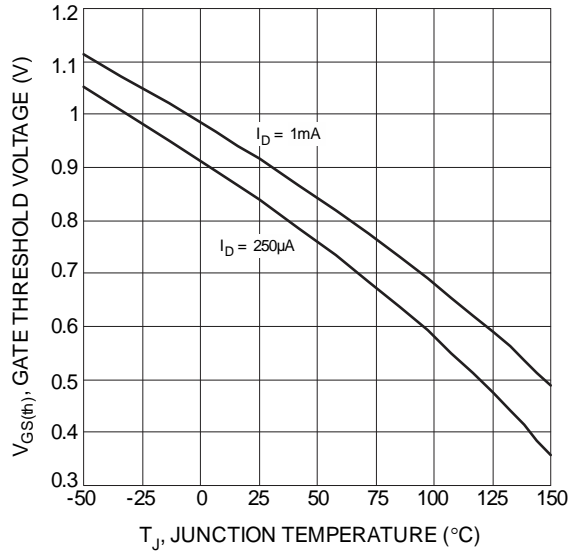


Figure 8 Gate Threshold Variation vs. Ambient Temperature

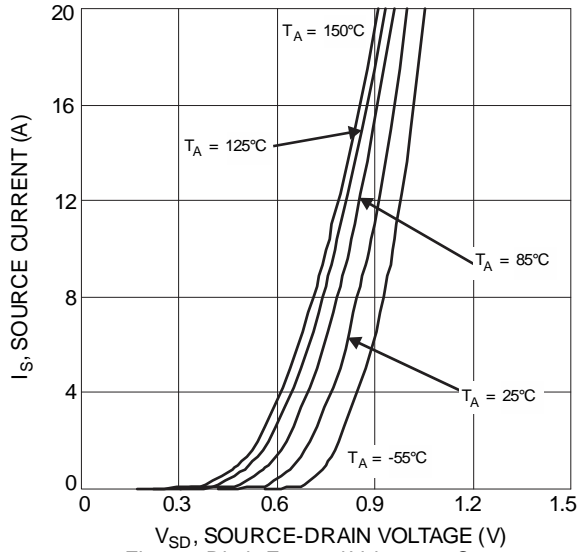


Figure 9 Diode Forward Voltage vs. Current

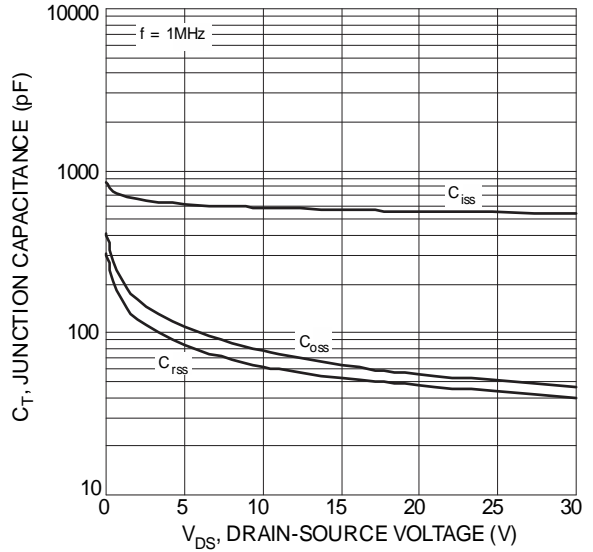


Figure 10 Typical Junction Capacitance

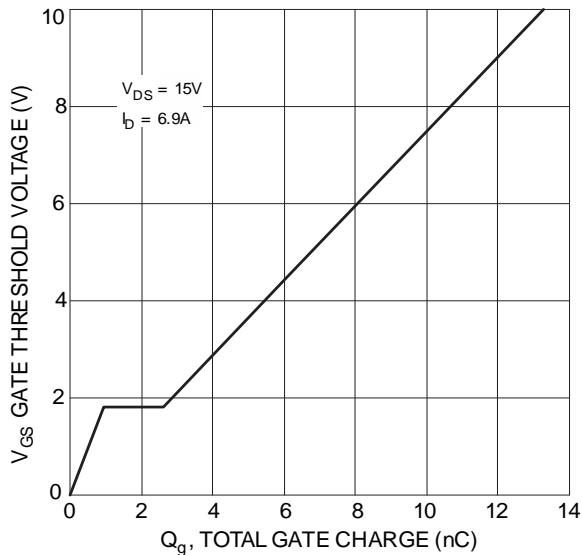


Figure 11 Gate Charge

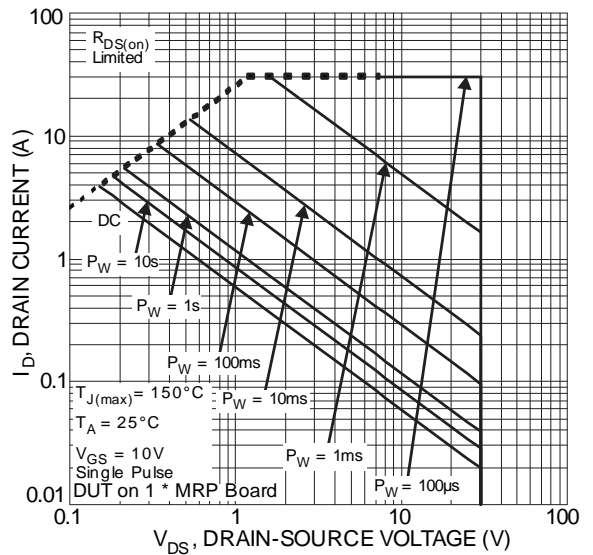
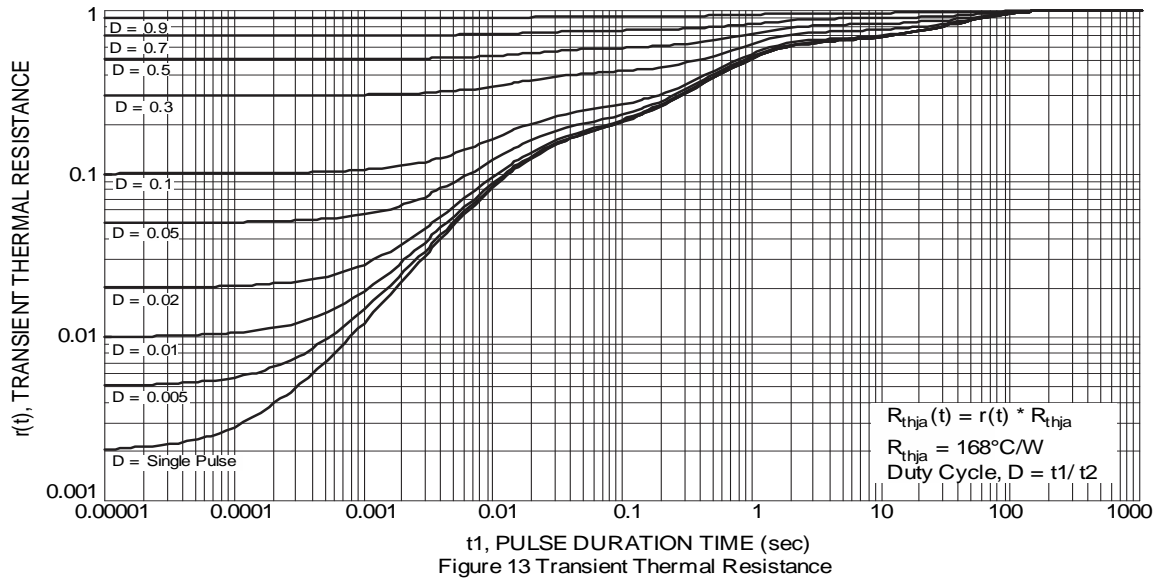


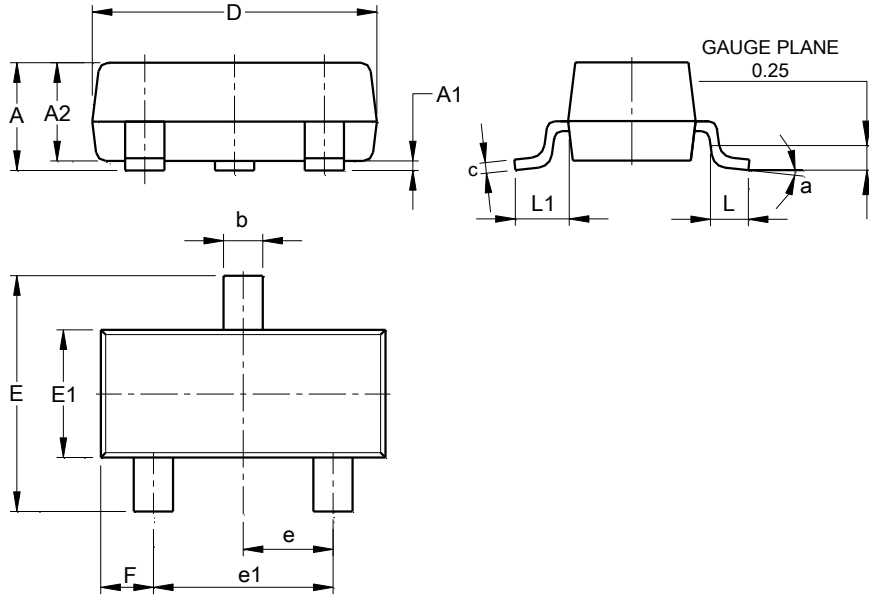
Figure 12 SOA, Safe Operation Area



**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

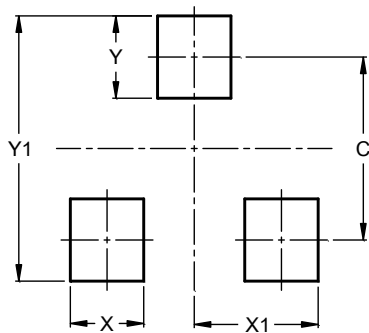
**SOT23 (Standard)**



SOT23 (Standard)			
Dim	Min	Max	Typ
A	0.90	1.15	1.025
A1	0.00	0.10	0.05
A2	0.85	1.10	0.975
b	0.30	0.51	0.40
c	0.080	0.202	0.11
D	2.80	3.00	2.90
E	2.25	2.55	2.40
E1	1.20	1.40	1.30
e	0.89	1.03	0.915
e1	1.78	2.05	1.83
F	0.40	0.60	0.535
L1	0.45	0.61	0.55
L	0.25	0.55	0.40
a	0°	8°	--
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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